

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLW34** is Designed for use in UHF amplifiers up to 860 MHz.

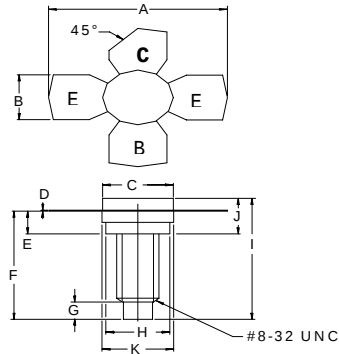
FEATURES:

- $P_G = 10.2$ dB Typical at 860 MHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	3.5 A
V_{CB}	50 V
P_{DISS}	31 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	5.6 $^\circ\text{C/W}$

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 60$ mA	30			V
BV_{CES}	$I_C = 8.0$ mA $V_{BE} = 0$ V	50			V
BV_{EBO}	$I_E = 4.0$ mA	4			V
I_{CES}	$V_{CE} = 30$ V			2	mA
h_{FE}	$V_{CE} = 25$ V $I_C = 600$ mA	20	40		---
C_c	$V_{CB} = 25$ V $f = 1.0$ MHz		13.5		pF
C_{re}			8.4		
C_{cs}			1.2		
GP	$V_{CE} = 25$ V $P_{OUT} 2.15$ W $I_C = 600$ mA $f = 224$ MHz		10.2		dB